Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Withdrawn) A method for producing an electrical leadframe (10) for a light-emitting diode component, the electrical leadframe having at least one first electrical connection conductor (2) and at least one second electrical connection conductor (3), the method comprising:

a) producing a layer composite comprising an electrically insulating carrier layer (101) and an electrically conductive connection conductor layer (102);

b) patterning of the carrier layer (101) in such a way that a contact-making window (7) to the connection conductor layer (102) is produced in said carrier layer; and

c) patterning of the connection conductor layer (102) in such a way that the first electrical connection conductor (2) and the second electrical connection conductor (3) are produced, and at least one of first and second electrical connection conductors can be electrically connected through the contact-making window (7).

2. (Withdrawn) The method as claimed in claim 1, wherein patterning of the connection conductor layer includes producing the first electrical connection conductor (2) and the second electrical connection conductor (3) such a way that an inner surface of at least one of first and second electrical connection conductors is exposed through the contact-making window.

3. (Withdrawn) The method as claimed in claim 1, in which step c) takes place before step b).

4. (Withdrawn) The method as claimed in claim 1, in which the carrier layer (101) consists essentially of a plastic film and the connection conductor layer (102) consists essentially of a metal film.

5. (Withdrawn) The method as claimed in claim 4, in which a thickness of the carrier layer (101) is less than 80 μm.

6. (Withdrawn) The method as claimed in claim 5, in which the thickness of the carrier layer (101) is between from and including 30 μm and up to and including 60 μm.

7. (Withdrawn) The method as claimed in claim 4, in which a thickness of the connection conductor layer (102) is less than 80 μm.

8. (Withdrawn) The method as claimed in claim 7, in which the thickness of the connection conductor layer (102) is between from and including 30 μm and up to and including 60 μm.

9. (Withdrawn) The method as claimed in claim 1, in which patterning the carrier layer includes forming a first contact-making window (7) and a second contact-making window (8) in the carrier layer (101) leading to the first connection conductor (2) and to the second connection conductor (3), respectively.

10. (Withdrawn) The method as claimed in claim 1, in which the carrier layer (101) is a plastic layer that can be patterned by means of masking and etching techniques.

11. (Withdrawn) The method as claimed in a claim 10, in which a portion of the plastic layer (101) corresponding to at least the contact-making window (7) comprises an uncured and etchable plastic, and wherein the patterning step includes curing or incipiently

curing the plastic layer except for a region (70) of the plastic layer corresponding to at least the contact-making window (7) and subsequently removing the region that was not cured or incipiently cured.

12. (Withdrawn) The method as claimed in claim 11, in which the patterning step includes applying a photoresist mask layer (103) to the plastic layer, patterning or applying the mask layer (103) in such a way that the region (70) of the plastic layer is covered by the mask layer (103), exposing the plastic layer and mask layer to radiation so that the plastic layer except for the region covered by the mask layer is incipiently cured or cured.

13. (Withdrawn) The method as claimed in claim 11, in which the patterning step includes positioning a photomask (104) above or on said plastic layer, the photomask shading the region (70) of the plastic layer, exposing the plastic layer and photomask to radiation so that the plastic layer except for the region shaded by the photomask is cured or incipiently cured or cured, and lifting off the photomask layer (104).

14. (Withdrawn) The method as claimed in claim 11, in which the plastic layer is cured or incipiently cured by UV radiation (105).

15. (Withdrawn) The method as claimed in claim 11, in which the plastic layer is cured or incipiently cured by thermal radiation.

16. (Withdrawn) The method as claimed in claims 11, in which the plastic layer includes a polyimide monomer.

17. (Withdrawn) The method as claimed in at least one of claims 11, in which removing from the connection conductor layer (102) by means of etching (106).

18. (Withdrawn) The method as claimed in at least one of claim 11, in which removing the region that was not cured or incipiently cured includes etching the plastic layer.

19. (Withdrawn) A method for producing a leadframe strip (200) having a multiplicity of component regions (202), at least one contact-making window (7) and at least two electrical connection conductors (2, 3) being formed in each component region (202) by means of the method as claimed in claim 1.

20. (Withdrawn) The method as claimed in claim 19, in which the connection conductor layer (102) is at least partly removed along separating lines (110) between in each case two adjacent component regions.

21. (Currently Amended) A method for producing a surface-mountable semiconductor component, ~~having at least one semiconductor chip (1), at least two external electrical connection conductors (2, 3), which are connected to at least two electrical contacts (4, 5) of the semiconductor chip (1), and having a chip housing (11) having a connection carrier (9) and a chip encapsulation (6), the method~~ comprising:

a) applying an electrically insulating carrier layer (101) to an electrically conductive connection conductor layer (102), patterning at least one chip window (7) and at least one wire connection window (8) in the carrier layer (101), and patterning ~~the~~ external electrical connection conductors (2,3) in[[to]] the connection conductor layer (102);

b) mounting ~~the~~ a semiconductor chip (1) on a first side of one of the connection conductors (2) through ~~into~~ the chip window (7), wherein the semiconductor chip is capable of emitting and/or receiving electromagnetic radiation;

c) electrically connecting at least one electrical contact (5) of the semiconductor chip (1) to at least one of the ~~a~~ connection conductors (3) by means of a bonding wire (50) through the wire connection window (8);

d) placing the ~~composite comprising patterned~~ connection conductor layer (102), ~~patterned~~ carrier layer (101), semiconductor chip (1) and bonding wire (50) into an injection mold; and

e) encapsulating the semiconductor chip (1) ~~including~~ and bonding wire (50) with an encapsulation material (6) by injection molding, ~~which~~ wherein the encapsulation material is transparent, and ~~is~~ subsequently at least partly ~~cured~~ or incipiently ~~cured~~curing the material, wherein subsequent to the encapsulation step, the connection conductors (2,3) on a side opposite to the first side are exposed for electrical connection to an electrical component.

22. (Currently Amended) The method as claimed in claim 21 ~~for simultaneously producing a multiplicity of semiconductor components, further comprising~~wherein:

in step a) producing an array (201) with a multiplicity of component regions (202), each component region (202) including ~~with in each case~~ at least one chip window (7), at least one wire connection window (8) and at least two external electrical connection conductors (2, 3) ~~in a composite with a connection conductor layer (102) and a carrier layer~~;

in steps b) and c), mounting a multiplicity of semiconductor chips (1) into a multiplicity of ~~the~~ chip windows (7) and connecting an electrical contact[[s]] (5) of ~~the~~ each semiconductor chip[[s]] (1) to one of the external electrical connections (3) by means of a ~~multiplicity of~~ bonding wire[[s]] (50);

in step d), placing the array into an injection mold (500), in which a single cavity (501) ~~which~~ spans ~~all~~ the multiplicity of component regions (202) of the array (201) and forms a void ~~there~~ over the component regions ~~essentially~~ exclusively on ~~the~~ a side of the carrier layer on which the semiconductor chips are mounted~~semiconductor chips (1) is provided for the entire array (201)~~; and

in step e), introducing the encapsulation material (6[[0]]) into the cavity (501) by injection molding and at least partly curing or incipiently curing the encapsulation material in the cavity; ~~and~~ the method further comprising;

removing the array (201) from the injection mold (500) and singulating the array into mutually separate semiconductor components by severing the encapsulation material (6[[0]]) and the carrier layer (101).

23. (Currently Amended) A method for producing a surface-mountable semiconductor component, ~~having at least one semiconductor chip (1), at least two external electrical connection conductors (2, 3), which are connected to at least two electrical contacts (4, 5) of the semiconductor chip (1), and having a chip housing (11) having a connection carrier (9) and a chip encapsulation (6), the method~~ comprising:

a) applying an electrically insulating carrier layer (101) to an electrically conductive connection conductor layer (102), patterning at least one chip window (7) in the carrier layer (101), and patterning ~~the~~ external electrical connection conductors (2, 3) into the connection conductor layer (102), the ~~two~~ connection conductors (2, 3) partly overlapping the chip window (7);

b) mounting ~~the~~ a semiconductor chip capable of emitting and/or receiving electromagnetic radiation onto the external electrical connection conductors (2, 3) in the chip window (7), in such a way that a first contact (4) and a second contact (5) of the semiconductor chip (1) ~~bear on the~~ are electrically connected to first sides of a first (2) and, respectively, ~~on the~~ a second (3) of the ~~two~~ connection conductors ~~(3) and are electrically connected thereto~~;

c) placing the ~~composite comprising patterned~~ connection conductor layer (102), ~~patterned~~ carrier layer (101) and semiconductor chip (1) into an injection mold (500); and

d) encapsulating the semiconductor chip (1) with a[[n]] transparent encapsulation material (6) by injection molding, ~~which material is~~ and subsequently at least partly ~~cured~~ or incipiently ~~cured~~curing the material, wherein subsequent to the encapsulation step, sides opposite to the first sides of the connection conductors are exposed for electrical connection to an electrical component.

24. (Currently Amended) The method as claimed in claim 23 ~~for simultaneously producing a multiplicity of semiconductor components using a method, further comprising,~~ wherein:

in step a), producing an array (201) with a multiplicity of component regions (202), each component region (202) including ~~with in each case~~ at least one chip window (7) and at least two external electrical connection conductors (2, 3) ~~in a composite with a connection conductor layer (102) and a carrier layer (101);~~

in step b), mounting a multiplicity of semiconductor chips (1) into ~~the~~ a multiplicity of chip windows (7) and connecting the chips to the ~~associated~~ connection conductors (2, 3);

in step c), placing the array into an injection mold (500), in which a single cavity (501) ~~which~~ spans ~~all~~ the multiplicity of semiconductor chips (1) of the array (201) and forms a void ~~there essentially exclusively on the side of~~ over the semiconductor chips (1) ~~is provided for the entire array (201);~~ and

in step d), introducing an encapsulation material (6[[0]]) into the cavity (501) by injection molding and at least partly curing or incipiently curing the encapsulation material in the cavity; ~~and~~ the method further comprising:

removing the array (201) from the injection mold (500) and singulating the array into mutually separate semiconductor components by severing the encapsulation material (6[[0]]) and the carrier layer.

25. (Currently Amended) The method as claimed in either claim 21 or 23, in which the semiconductor chip[[s]] (1) comprises a light-emitting diode chip[[s]].

26. (Currently Amended) The method as claimed in claim ~~25~~23, wherein mounting a semiconductor chip includes mounting a light-emitting diode chip having a light-generating epitaxial layer, in which the light-emitting diode chip~~s are~~ is mounted onto the external electrical connection[[s]] conductor in rotated fashion with the light-generating epitaxial layer[[s]] facing toward said connection[[s]] conductor.

27. (Original) The method as claimed in either claim 21 or 23, in which the carrier layer (101) consists essentially of a plastic film and the connection conductor layer (102) consists essentially of a metal film.

28. (Original) The method as claimed in claim 27, in which a thickness of the carrier layer (101) is less than 80 μm.

29. (Original) The method as claimed in claim 28, in which the thickness of the carrier layer is between from and including 30 μm and up to and including 60 μm.

30. (Original) The method as claimed in claims 27, in which a thickness of the connection conductor layer (102) is less than 80 μm.

31. (Original) The method as claimed in claim 30, in which thickness of the connection conductor layer (102) is between from and including 30 μm and up to and including 60 μm.

32. (Currently Amended) The method as claimed in ~~either~~ claim 21 ~~or 23, in which a first contact-making window (7) and a second contact-making window (8) are formed in the carrier layer (101),~~wherein the chip window (7) ~~which windows~~ leads to ~~the~~ a first of the connection conductors (2) and the wire connection window (8) leads to a ~~the~~ second of the connection conductors (3), respectively.

33. (Original) The method as claimed in either claim 21 or 23, in which the carrier layer (101) comprises a plastic layer that can be patterned by means of masking and etching techniques.

34. (Currently Amended) The method as claimed in a claim 33, in which a portion of the plastic layer (101) corresponding to at least the ~~contact-making~~ chip window (7) comprises an uncured and etchable plastic, and wherein the patterning step includes curing or incipiently curing the plastic layer except for a region (70) of the plastic layer corresponding to at least the ~~contact-making~~ chip window (7) and subsequently removing the region that was not cured or incipiently cured.

35. (Currently Amended) The method as claimed in claim 34, in which the patterning step includes applying a photoresist mask layer (103) to the plastic layer, patterning or applying the mask layer (103) in such a way that the region (70) of the plastic layer is covered by the mask layer (103), and exposing the plastic layer and mask layer to radiation so that the plastic layer except for the region covered by the mask layer is incipiently cured or cured.

36. (Currently Amended) The method as claimed in claim 34, in which the patterning step includes positioning a photomask (104) above or on said plastic layer, the photomask shading the region (70) of the plastic layer, exposing the plastic layer and photomask to radiation so that the plastic layer except for the region shaded by the photomask is cured or incipiently cured or cured, and lifting off the photomask ~~layer~~ (104).

37. (Original) The method as claimed in claim 33, in which the plastic layer is cured or incipiently cured by UV radiation (105).

38. (Original) The method as claimed in claim 33, in which the plastic layer is cured or incipiently cured by thermal radiation.

39. (Original) The method as claimed in claim 27, in which the plastic layer includes a polyimide monomer.

40. (Original) The method as claimed in claim 27, in which removing the region that was not cured or incipiently cured includes etching the plastic layer.

41. (Withdrawn) A leadframe strip (200) having a connection conductor layer (102) and a carrier layer (101), on which an array (201) with a multiplicity of component regions (202) is formed, the connection conductor layer (101) being at least partly removed along separating lines (110) between adjacent component regions (202).

42. (Withdrawn) The leadframe strip as claimed in claim 41, in which the connection conductor layer (102) is produced from a patterned metal film.

43. (Withdrawn) The leadframe strip as claimed in claim 42, in which the carrier layer (101) is produced from a patterned plastic film.

44. (Withdrawn) The leadframe strip as claimed in claim 43, in which the plastic film includes a polyimide material.

45. (Withdrawn) The leadframe strip as claimed in claim 44, in which the plastic film is patterned by means of photolithography technology.